AMENDMENTS

In the Claims:

1. (Currently Amended) A semiconductor light emitting device comprising:

a semiconductor substrate;

a first multilayered reflection film on the semiconductor substrate;

a light emission layer on the first multilayered reflection film;

a second multilayered reflection film made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], on the light emission layer;

a semiconductor layer on the second multilayered reflection film; and

a current constriction layer on the semiconductor layer,

wherein the first multilayered reflection film and the second multilayered reflection film form a resonator with a specified interval, and the light emission layer is formed in a position of an antinode of a standing wave inside the resonator, and

wherein the semiconductor layer has a value obtained by dividing resistivity by thickness being 1×10^3 Ω or more.

2. (Currently Amended) A semiconductor light emitting device comprising:

a semiconductor substrate;

a first multilayered reflection film on the semiconductor substrate;

a light emission layer on the first multilayered reflection film;

a second multilayered reflection film made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], on the light emission layer; ~~and~~

~~a current constriction layer~~ a semiconductor layer on the second multilayered reflection film said semiconductor layer having a carrier density; and

a current constriction layer on the semiconductor layer,

wherein the first multilayered reflection film and the second multilayered reflection film form a resonator with a specified interval, and the light emission layer is formed in a position of an antinode of a standing wave inside the resonator, and

wherein said carrier density of the semiconductor layer is set such that a percentage of a current diffused to an outside of a current flow pass formed in the current constriction layer is 25% or less of a total current applied to the current flow pass.

3. (Original) The semiconductor light emitting device as defined in Claim 1, further comprising a current diffusion layer on the current constriction layer.

4. (Original) The semiconductor light emitting device as defined in Claim 2, further comprising a current diffusion layer on the current constriction layer.

5. (Currently Amended) The semiconductor light emitting device as defined in Claim 1, wherein

the semiconductor substrate is made of GaAs,

the light emission layer is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], and

~~between the second multilayered reflection film and the current constriction layer, there is provided a~~ the semiconductor layer is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], or GaP.

6. (Currently Amended) The semiconductor light emitting device as defined in Claim 2, wherein

the semiconductor substrate is made of GaAs,

the light emission layer is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], and

~~between the second multilayered reflection film and the current constriction layer, there is provided a~~ the semiconductor layer is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], or GaP.

7. (Currently Amended) The semiconductor light emitting device as defined in Claim 1, wherein

the semiconductor substrate is made of GaAs,

~~between the second multilayered reflection film and the current constriction layer, there is provided a~~ the semiconductor layer is made of $Al_yGa_zIn_{1-y-z}P$ ($O \leq y \leq 1$, $0 \leq z \leq 1$) or GaP, and

the current constriction layer is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], or GaP.

8. (Currently Amended) The semiconductor light emitting device as defined in Claim 2, wherein

the semiconductor substrate is made of GaAs,

~~between the second multilayered reflection film and the current constriction layer, there is provided a~~ the semiconductor layer is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], or GaP, and

the current constriction layer is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], or GaP.

9. (Currently Amended) The semiconductor light emitting device as defined in Claim 1, wherein

the semiconductor substrate is made of GaAs,

~~between the second multilayered reflection film and the current constriction layer, there is provided a~~ the semiconductor layer is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], or GaP,

a current diffusion layer is provided on the current constriction layer, and

~~the current diffusion layer~~ is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]].

10. (Currently Amended) The semiconductor light emitting device as defined in Claim 2, wherein

the semiconductor substrate is made of GaAs,

~~between the second multilayered reflection film and the current constriction layer, there is provided a~~ the semiconductor layer is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]], or GaP,

a current diffusion layer is provided on the current constriction layer, and

the current diffusion layer is made of $Al_yGa_zIn_{1-y-z}P$, [[(]] wherein $0 \leq y \leq 1$[[,]] and $0 \leq z \leq 1$[[)]].

11. (New) The semiconductor light emitting device as defined in Claim 2, wherein the carrier density is 1×10^{18} cm $^{-3}$.